

FAR-IR, SUBMM, & MM DETECTOR TECHNOLOGY WORKSHOP



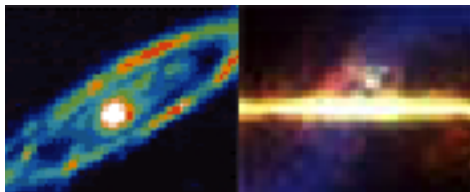
FILLED BOLOMETER ARRAYS FOR THE HERSCHEL/PACS PHOTOMETER

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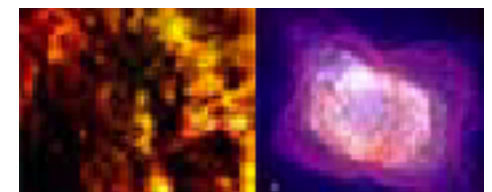
SAP/DAPNIA CEA SACLAY



Organized & Sponsored by NASA/Ames & USRA/SOFIA

1 - 3 April 2002

Monterey, California



Detector design drivers

Large format to achieve PSF full sampling
Good production yield
Possibility of space qualification
High background applications ($\text{NEP} = 10^{-16} \text{ W Hz}^{-0.5}$)
Operating temperature at 300 mK

Design main features

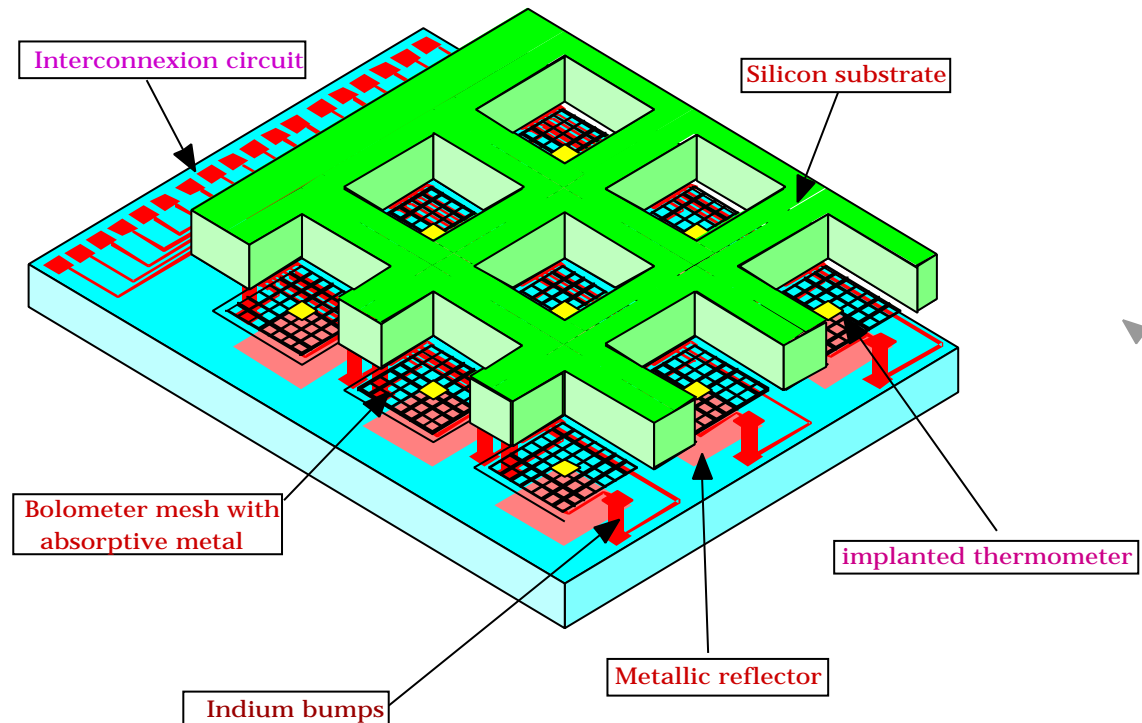
All Silicon technology

Absorption in resonant metal mesh supported by suspended silicon grids

Thermometer in compensated implanted Si

Quarter wave cavity by indium bump

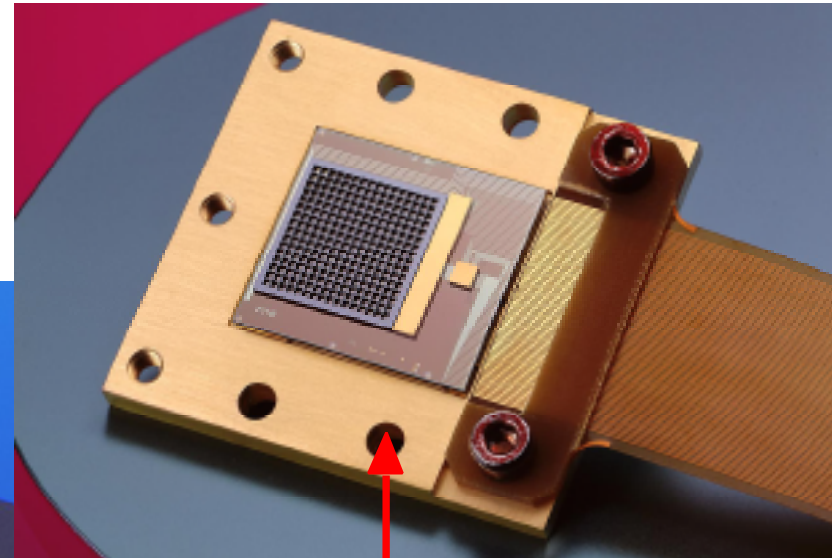
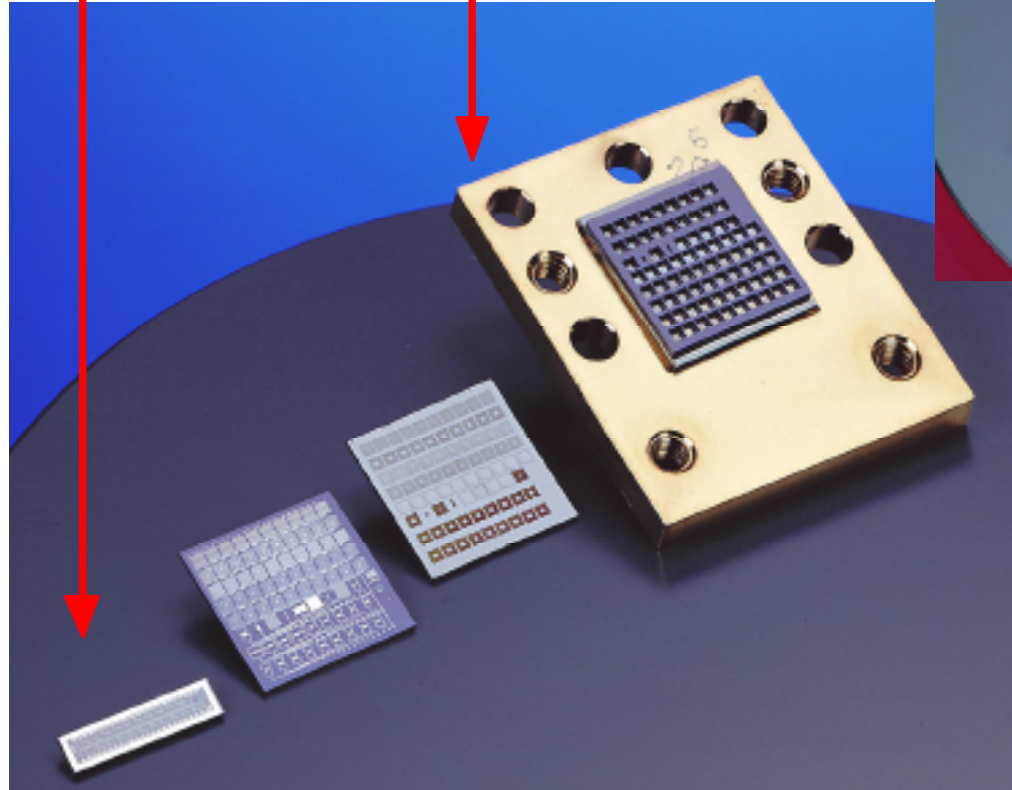
Cold readout and multiplexer electronics in Si MOS technology



Technology evolution since 1997

1997

1998



1999

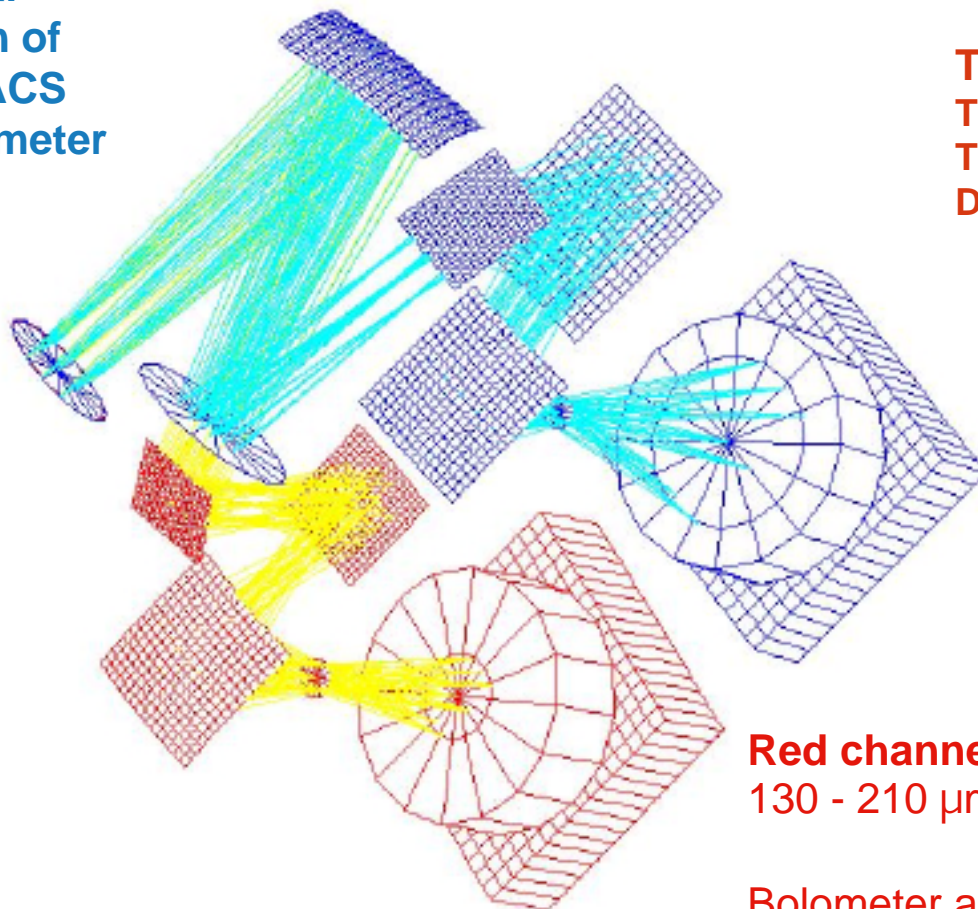
PACS on Herschel

A photometer and spectrograph instrument in the Far-infrared (60 - 200 μm)

PI Albretch Potglitch, MPE, Garching, Germany

Bolometers are used on the photometers
Photoconductors are used on the spectrograph

**Optical
design of
the PACS
photometer**



The two bolometer arrays have
The same pixel pitch
The same cold readout electronics
Different grid design

Blue channel

60 - 90 μm

90 - 130 μm

Bolometer array : 32 x 64

Red channel

130 - 210 μm

Bolometer array : 16 x 32

Improvements for the PACS bolometer design

New grid design adapted to the PACS wavelengths

SI grid and thermometer manufactured on a double SOI wafer

New design of mechanical support to ensure 3 side buttability : (gap $750\text{ }\mu\text{m}$ = 1 pixel)

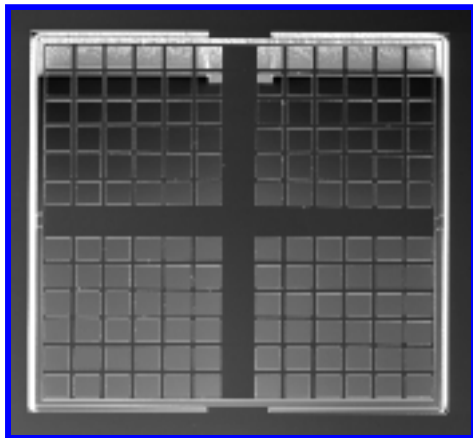
MOS follower and multiplexer implanted in the interconnection circuit

MOS preamplifier at 2K

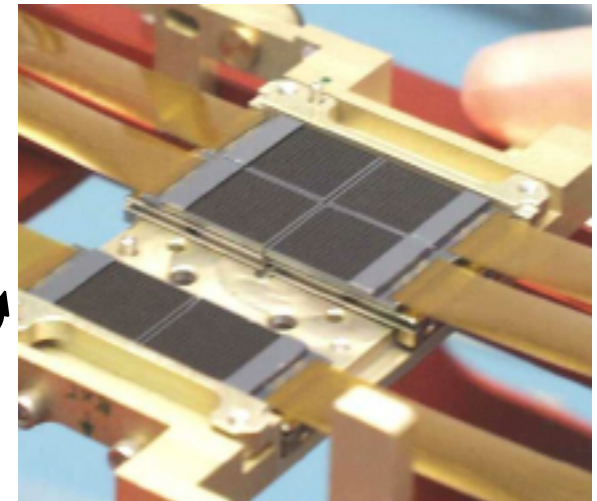
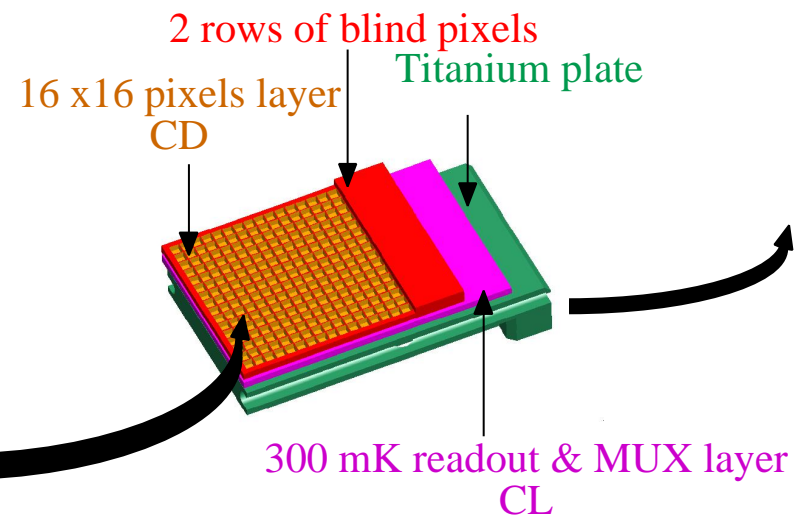
Mechanical support and mounting tools for array manufacturing

BLUE ARRAY CONFIGURATION

THE PIXEL



THE 16 X 18 SUB-ARRAY



PACS bolometer pixel design

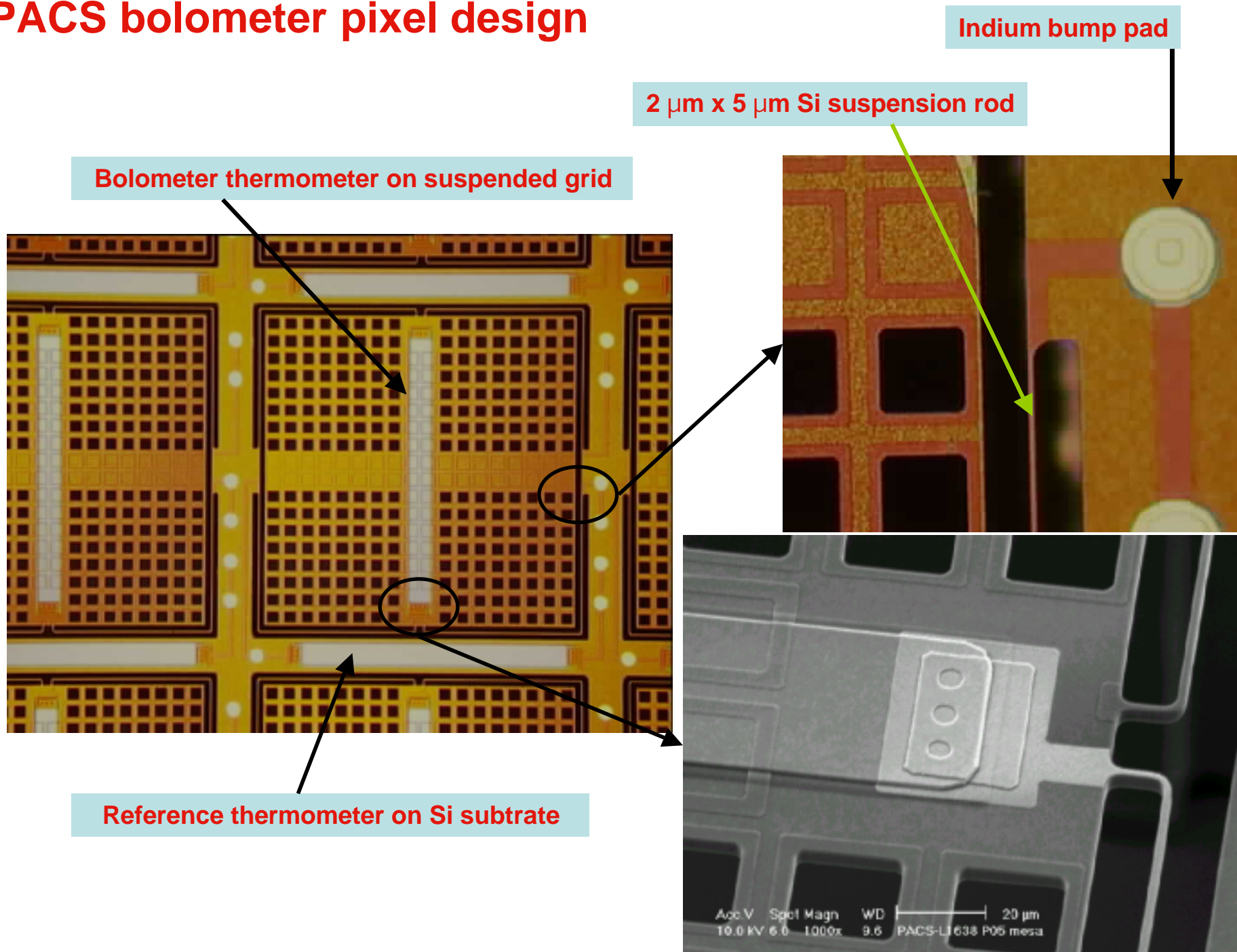
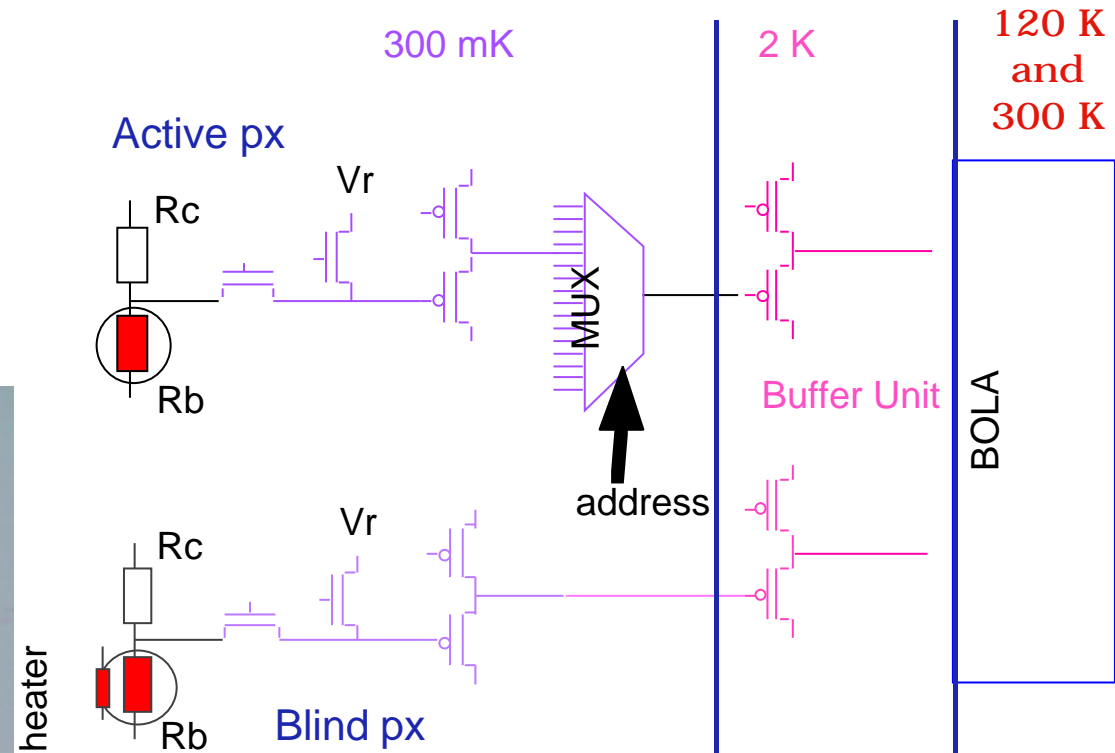
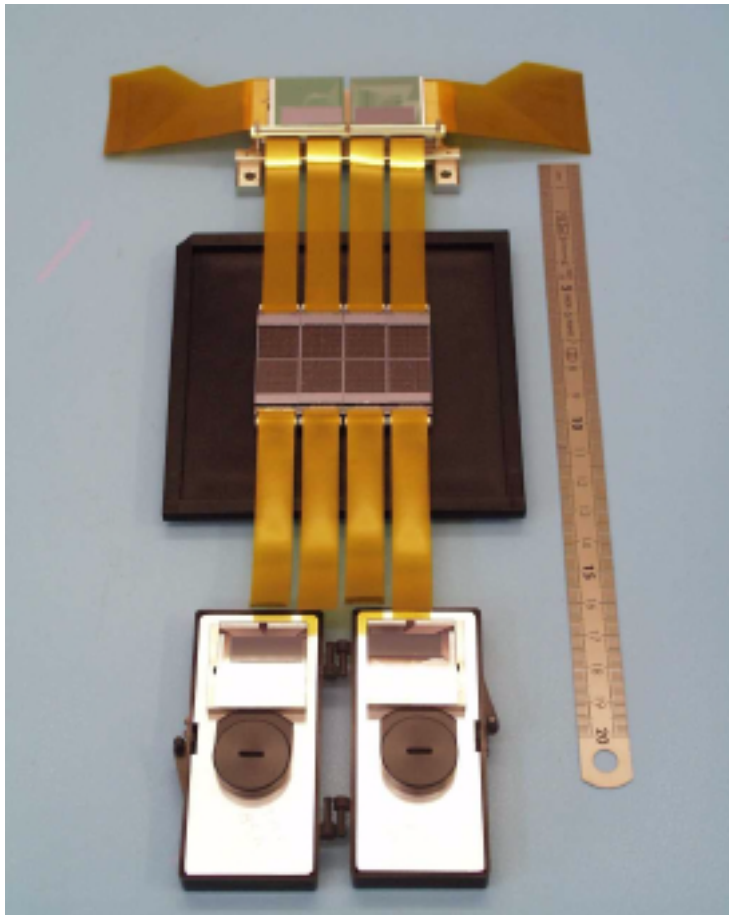


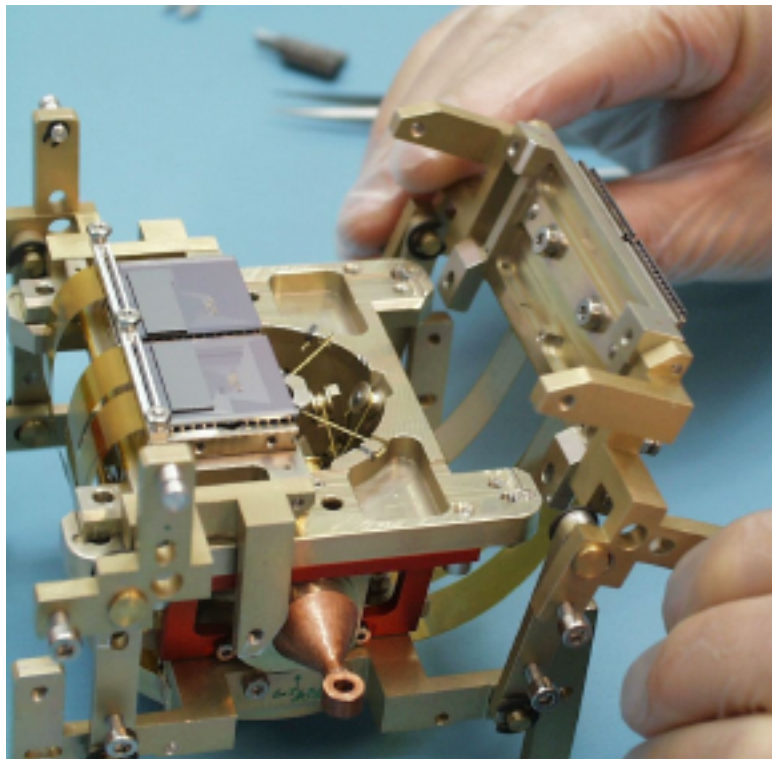
Figure 1 is a line graph titled "Blue and Red Focal Planes". The y-axis is labeled "Absorption" and ranges from 0 to 1.0 in increments of 0.1. The x-axis is labeled "wavelength in microns" and ranges from 0 to 400 in increments of 50. There are two data series: a blue line representing "cavity = 20 microns" and a red line representing "cavity = 25 microns". Both curves show a sharp rise in absorption starting around 50 microns, peaking near 1.0 at approximately 100 microns, and then gradually decreasing. The 25 micron cavity curve remains slightly higher than the 20 micron cavity curve in the 100-400 micron range.

Readout and signal processing



The cold electronic system ensures

- a) the double correlated sampling to remove $1/f$ readout noise,**
- b) fully differential measurement with blind pixels to remove the external collective perturbations.**
- c) 16 -> 1 Multiplexing.**

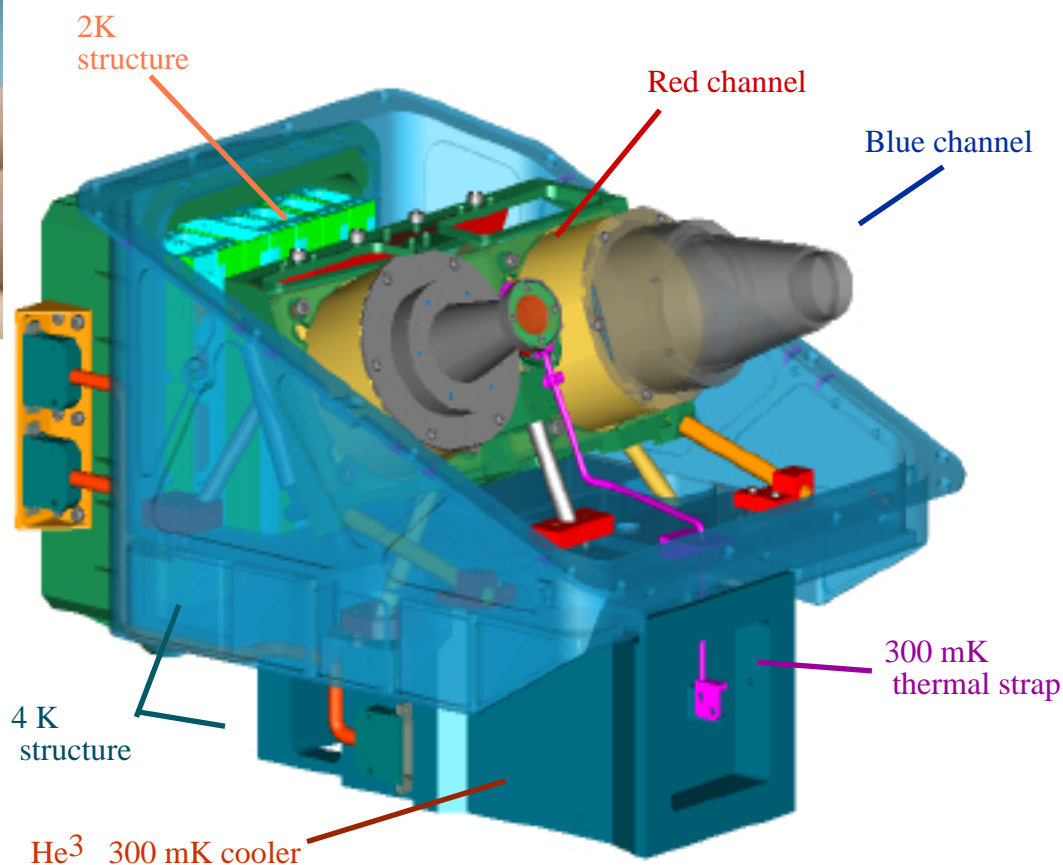


MECHANICAL & THERMAL DESIGN

Mounting of the arrays and associated 2K preamplifier

The 300 mK thermal stage is insulated from the 2 K stage thanks to kevlar® wires

The suspension scheme was qualified in vibration tests at the ARIANE V nominal levels at warm temperature.



PACS Focal plane

FIRST RESULTS

All the pixel functionalities checked operational at 300 mK:
differential mode, double correlated sampling, multiplexing.

Thermal design: Demonstrated. A simplified array in operation achieved 280 mK on a 2 STP liter cryocooler.

Responsivity: Measured response to a bare 20 K blackbody: 10^{10} V/W. This value should be better in the photometer bands (filters not yet availables).

2 K Buffer Noise: The Buffer noise density was measured at 4K to be lower than $0.5 \mu\text{V/ Hz}$ @ 2 Hz

2 K Buffer Bandwidth & dissipated power:

The Buffer bandwidth with an output capacitance of 1 nf was measured to be 5,5 kHz (needed 3 kHz), for a total power charge on the 2K level of 2,8 mW (3.3 mW max allowed power for 2500 pixels).

PROSPECTS

The noise performances of the implanted Si thermometer and their associated MOS cold electronics are good enough to achieve BLIP conditions under high background conditions, like in HSO or for direct imagery on ground based telescope.

The all Si based technology is the natural choice to manufacture large arrays with a good yield.

The vacuum resonant cavity achieved by indium bump can be adapted from 100 μm to 850 μm . It cannot be extended beyond 1 mm

A larger focal plane (4000 px) is foreseen for a balloon experiment: ELISA, in a wider wavelength range (100 μm - 800 μm) (PI: I. Ristorcelli, CESR, France).